Claims

1."canceled".

2."currently amended". A transistor comprising elements of bipolar static induction transistors: [[two]] a gate, [[four]] sources and channels ~~and six electrodes~~ on either side of a lightly doped n-type silicon monocrystal substrate;

one ~~of said~~ channel of the multielement structure is thicker than the other normally-off channels on either side of said substrate;

said ~~thick channels are~~ channel is connected to a separate electrode on either side of said substrate.

3."canceled".

4."currently amended". The transistor according to claim 2 wherein an epitaxial ~~layers~~ layer of the same type of conductivity with the impurity concentration of about 10.sup.17 cm.sup.-3 [[are]] is disposed on either side of said substrate;

said [[gates]] gate , said sources and said channels are disposed in said epitaxial ~~layers~~ layer.

5."previously presented". The transistor according to claim 2 wherein a layer of a doped n+-type polysilicon is disposed on the silicon monocrystal surface.

6."currently amended". The transistor according to claim 2 wherein the control over both hole emission into and extraction out the lightly doped area are used as well as the current feedback for said control over emission into one.

7."previously presented". The transistor according to claim 2 wherein the thickness of said channels are small and the impurity concentration near said gates is high enough.

8."previously presented". The transistor according to claim 4 wherein a layer of a doped n+-type polysilicon is disposed on the silicon monocrystal surface.

9."currently amended". The transistor according to claim 4 wherein said thick ~~channels are~~ channel is normally-on [[ones]] one.

AUTHOR: 05.28.2004 EDLIN S.D.